

# A Triatomic Silicon(0) Cluster Stabilized by a Cyclic Alkyl(amino) Carbene

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Dedicated to Dr. Richard Weidner

**Abstract:** Reduction of the neutral carbene tetrachlorosilane adduct (cAAC)SiCl<sub>4</sub> (cAAC = cyclic alkyl(amino) carbene :C(CMe<sub>2</sub>)<sub>2</sub>(CH<sub>2</sub>)N(2,6-iPr<sub>2</sub>C<sub>6</sub>H<sub>3</sub>)) with potassium graphite produces stable (cAAC)<sub>3</sub>Si<sub>3</sub>, a carbene-stabilized triatomic silicon(0) molecule. The Si–Si bond lengths in (cAAC)<sub>3</sub>Si<sub>3</sub> are 2.399(8), 2.369(8) and 2.398(8) Å, which are in the range of Si–Si single bonds. Each trigonal pyramidal silicon atom of the triangular molecule (cAAC)<sub>3</sub>Si<sub>3</sub> possesses a lone pair of electrons. Its bonding, stability, and electron density distributions were studied by quantum chemical calculations.

The major component (90%) of the earth's crust is made of silicates consisting of silicon(IV), which is the preferred oxidation state of silicon.<sup>[1]</sup> Reduction of silicon(IV) compounds (such as SiO<sub>2</sub> with charcoal at high temperature) or high-temperature chemical decomposition of SiCl<sub>4</sub> or HSiCl<sub>3</sub> leads to crystalline silicon(0), which is used for silicon chips in almost all electronic equipments.<sup>[2,3]</sup> Monocrystalline silicon has an extended diamondlike cubic crystal structure.<sup>[4]</sup> The optical and electronic properties of silicon-containing semiconductors originate from the molecular to macroscopic size regimes, and hence studies of silicon clusters are very important.<sup>[3,5]</sup> Small clusters consisting only of silicon atoms, which are generated in different ways for short periods of time, are of huge importance for numerous reasons. To date, these low-nuclearity silicon clusters have been characterized

only by spectroscopic methods and studied by theoretical calculations. Silicon clusters ranging from Si<sub>2</sub> to Si<sub>7</sub> are prepared by vapor deposition of amorphous silicon and were observed in the gas phase by mass spectrometry<sup>[6]</sup> or studied in neon and argon matrices.<sup>[7–8]</sup> They were also characterized by electronic absorption spectra in neon matrices at 5 K.<sup>[9]</sup> Larger ionic silicon clusters of up to 43 silicon atoms were generated by pulsed laser vaporization and detected by mass spectrometry studies.<sup>[10]</sup> In addition, small silicon clusters play an important role in the photochemistry of some silicon-rich evolved stars.<sup>[11]</sup> The Si<sub>3</sub> molecule is one of the most important-silicon based clusters. The most recent study on the Si<sub>3</sub> cluster was an investigation on a trapped sample in an inert gas matrix. On the basis of infrared spectroscopy, optical studies, and ab initio calculations, the molecule was found to be asymmetric with C<sub>2v</sub> symmetry.<sup>[12,13]</sup> Importantly, Si<sub>3</sub> is suspected to be an interstellar species<sup>[14,15]</sup> along with interstellar molecules C<sub>3</sub>, SiC<sub>2</sub>, SiC<sub>3</sub>, SiCN, and SiNC in space,<sup>[16,17]</sup> which were generally detected and studied by infrared, microwave, and radio wave spectroscopy. Molecular Si<sub>3</sub> was discovered among the reaction products when SiH<sub>4</sub> was discharged during an experiment to characterize new silicon hydrides.<sup>[12,13]</sup> Ab initio calculations predict that silicon-containing clusters are significantly different in structure and bonding from the analogous lighter carbon compounds.<sup>[7,18,19]</sup> For example, linear C<sub>3</sub> (**A**) is more stable than cyclic C<sub>3</sub>.<sup>[20]</sup> In contrast, bent Si<sub>3</sub> (**C**) is more stable by 9.5 kcal mol<sup>-1</sup> than its linear Si<sub>3</sub> (**B**) molecule (Scheme 1) with an extremely shallow bending potential.<sup>[12,13]</sup> All these reported species are not stable at room temperature and are not formed selectively. A C<sub>3</sub> molecule that is stable at room temperature and is stabilized by a neutral ligand has not been isolated to date.<sup>[20,21]</sup>

Singlet carbenes are a class of compounds which have a pair of electrons on a sp<sup>2</sup>-hybridized orbital of a divalent carbon atom.<sup>[22]</sup> They have become powerful tools for stabilization and isolation of extremely reactive unusual

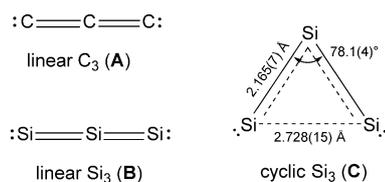
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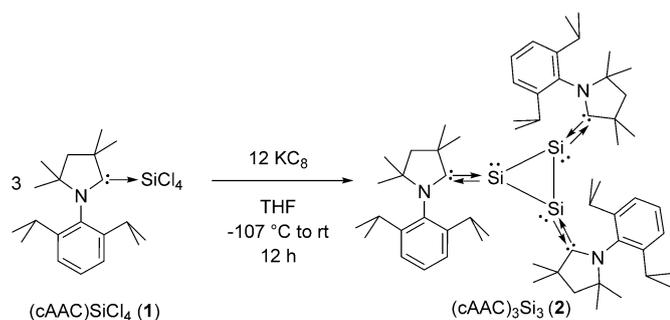
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Supporting information for this article (including UV/Vis spectrum, structural determination, and computational details for **2**) is available on the WWW under <http://dx.doi.org/10.1002/anie.201511019>.



Scheme 1. Linear and cyclic isomers of C<sub>3</sub> (**A**), and Si<sub>3</sub> (**B**, **C**) clusters.

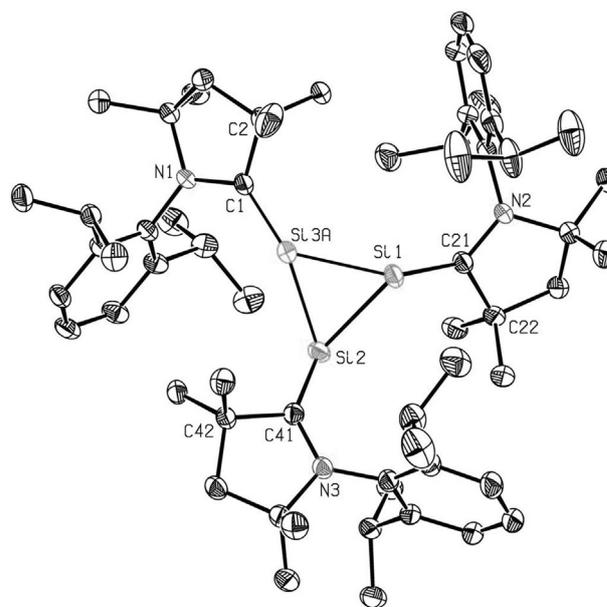


**Scheme 2.** Synthesis of compound **2**.

chemical species.<sup>[23]</sup> Monoatomic and diatomic silicon(0)<sup>[24,25]</sup> have been stabilized by carbenes such as *N*-heterocyclic carbenes and cyclic alkyl(amino) carbenes. Cyclic alkyl(amino) carbenes are inherently stronger  $\sigma$ -donors and better  $\pi$ -acceptors because of the presence of only one adjacent nitrogen atom in the molecule.<sup>[22]</sup> This property prompted us to utilize cyclic alkyl(amino) carbene (cAAC) stabilized (cAAC)SiCl<sub>4</sub><sup>[26]</sup> as a precursor for the synthesis of a triatomic silicon(0) compound (cAAC)<sub>3</sub>Si<sub>3</sub> (**2**; where cAAC = :C(CMe<sub>2</sub>)<sub>2</sub>(CH<sub>2</sub>)N(2,6-*i*Pr<sub>2</sub>C<sub>6</sub>H<sub>3</sub>)). Herein, we report on the preparation, synchrotron single-crystal X-ray diffraction study, and theoretical calculations of tris(cyclic alkyl(amino) carbene)trisilicon(0) (**2**; Scheme 2). This compound is stable, isolable, and storable at room temperature. Results on this Si<sub>3</sub> molecule should also provide a fundamental route for selectively preparing small single-cluster species, which will allow further synthetic endeavors at room temperature.

The <sup>29</sup>Si NMR spectrum of **2** in C<sub>6</sub>D<sub>6</sub> shows a singlet at +7.20 ppm which is downfield-shifted compared with that of precursor **1** (−103.5 ppm). However, it is upfield-shifted compared with those of cAAC-stabilized monoatomic ((cAAC)<sub>2</sub>Si; +66.71 ppm) and diatomic ((cAAC)<sub>2</sub>Si<sub>2</sub>; +254.60 ppm) silicon(0) compounds. The <sup>29</sup>Si NMR resonance of **2** is close to the value of +14.6 ppm reported for [PhC(N*t*Bu)<sub>2</sub>]<sub>2</sub>SiCl<sup>[27]</sup> but is observed at a considerably lower field than the value of +38.4 ppm reported for (NHC)<sub>2</sub>Si<sub>2</sub>Cl<sub>2</sub><sup>[25]</sup> and the value of +78.3 ppm reported for [C(H)N(*t*Bu)]<sub>2</sub>Si.<sup>[28]</sup> The resonance of the carbene carbon atom of **2** appears at +207.4 ppm, which is close to that of precursor **1** (+206.1 ppm).<sup>[26]</sup>

Single-crystal structural determination with synchrotron radiation,<sup>[29]</sup> followed by aspherical-atom least-squares refinement<sup>[30]</sup> and subsequent structural analysis of **2** showed that the triangular Si<sub>3</sub> unit is sterically well-shielded by three cAAC ligands. Each silicon atom is bonded to two adjacent silicon atoms and further bound to the carbene carbon atom of a cAAC ligand. Three cAAC ligands in **2** are oriented in a propeller fashion with respect to the center of the triangular Si<sub>3</sub> unit (Figure 1). None of the cAAC ligands is in the plane of the Si<sub>3</sub> unit. The Si–Si bond distances of **2** are 2.399(8) Å, 2.369(8) Å, and 2.398(8) Å, which are longer by about 0.04 Å than the sum of the Si covalent radii (2.34 Å)<sup>[31]</sup> and about 0.02 Å longer than the Si–Si single bond length in  $\alpha$ -silicon (2.36 Å).<sup>[32]</sup> Each silicon atom of **2** is in the formal oxidation



**Figure 1.** Molecular (ORTEP) view of carbene-stabilized triatomic silicon(0) (**2**) in the solid state (H atoms are omitted for clarity). Thermal ellipsoids represent 50% probability. Selected experimental bond distances [Å] and angles [°] [calculated at BP86/def2-SVP level] for **2** are Si1–Si2 2.399(8) Å [2.398], Si1–Si3A 2.369(8) Å [2.365], Si2–Si3A 2.398(8) Å [2.399], Si1–C21 1.854(7) Å [1.855], Si2–C41 1.878(7) Å [1.892], Si3A–C1 1.834(7) Å [1.850], N1–C1 1.392(6) Å [1.392], N2–C21 1.385(6) Å [1.388], N3–C41 1.378(5) Å [1.373]; Si2–Si1–Si3A 60.4(3)° [60.5], Si1–Si2–Si3A 59.2(3)° [59.1], Si1–Si3A–Si2 60.4(3)° [60.4], N1–C1–C2 107.3(3)° [107.1], N2–C21–C22 107.3(3)° [107.9], N3–C41–C42 107.2(3)° [107.6].

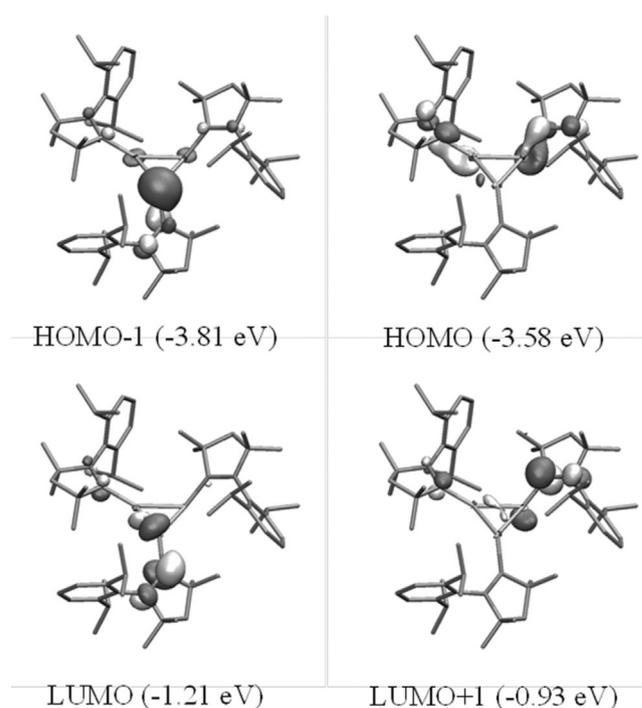
state zero and adopts a three-coordinate trigonal pyramidal structure. The sums of the bond angles of silicon atoms in **2** are 320.1°, 333.6°, and 292.0° (mean value of 315.2°). One of the silicon atoms (Si3) is slightly disordered. The pyramidal geometry at each silicon atom in **2** results from a lone pair of electrons (distances from Si atoms to corresponding triangular planes; Si1–Si2Si3AC21 0.663 Å, Si2–Si1Si3AC41 0.966 Å, Si3A–Si1Si2C1 0.541 Å). Two lone pairs of electrons of two silicon atoms (Si3A, Si1) are on the same side while the third one (Si2) is on the opposite side. Thus, **2** can be considered as a triangular trisilylene having 6  $\pi$  electrons. The triangular Si<sub>3</sub> unit of **2** is comparable to the graphene-like two-dimensional silicene<sup>[33]</sup> which has an extended nonplanar Si<sub>6</sub> unit (Si–Si distance 2.32 Å) with a Si<sub>3</sub> fragment over three silver atoms of the silver(111) substrate. The silicon–carbon distances are 1.854(7), 1.878(7), and 1.834(7) Å which are comparable to those of cAAC-stabilized monoatomic and diatomic silicon(0) compounds.<sup>[24–25]</sup> The average silicon–carbon bond length of **2** is shorter than that of precursor **1** (about 1.94 Å). The average carbon–nitrogen bond length of **2** is 1.38 Å, which is longer by about 0.08 Å than that of **1**, thus suggesting significant  $\pi$  back-donation from each silicon atom to carbene carbon atom.

We carried out quantum chemical calculations using density functional theory at the BP86/def2-SVP level in order to analyze the bonding situation in **2**. The calculated bond lengths and angles are in excellent agreement with the

experimental data (Figure 1). The natural bond orbital (NBO) analysis suggests a rather uncomplicated picture of the core bonds in  $(\text{cAAC})_3\text{Si}_3$ . The relevant bond orbitals are shown in Figure S4 in the Supporting Information. The cyclic  $\text{Si}_3$  moiety features three Si–Si  $\sigma$ -bond orbitals that are slightly polar with degrees varying between 45–55% because of the asymmetry of the three Si(cAAC) moieties. The dative bonds of the ligands exhibit three  $\text{cAAC} \rightarrow \text{Si}$   $\sigma$ -donor bond orbitals that are polarized with 68–71% toward the carbon end. The  $\pi$ -type bond orbitals that arise from the  $\text{cAAC} \leftarrow \text{Si}$   $\pi$  back-donation are almost nonpolar (between 40–54% at Si) which indicates quite large  $\pi$  back-donation. This effect can be explained by the strong repulsion between the three formally lone-pair orbitals, which comes from the exchange (Pauli) repulsion, in the  $\text{Si}_3$  ring. Pyramidalization and strong  $\pi$  back-donation relieve the Pauli repulsion.<sup>[34]</sup> Compound **2** could thus also be depicted with Si=C double bonds. The  $^{15}\text{N}$  NMR resonance of **2** is observed at  $-233.0$  ppm (see the Supporting Information), which is upfield-shifted when compared to that of precursor **1** ( $-164.1$  ppm) but close to the value recorded for silylone<sup>[24]</sup>  $(\text{cAAC})_2\text{Si}$  ( $-230.0$  ppm). These values suggest that the  $\pi$  back-donation from silicon atom to carbene carbon atom ( $\text{C}_{\text{cAAC}} \leftarrow \text{Si}$ ) of **2** is similar in magnitude to that of  $(\text{cAAC})_2\text{Si}$ . However, the dissociation of the cAAC ligands smoothly leads to the fragments  $\text{Si}_3$  and 3 cAAC in the singlet states, which supports the description with coordinate bonds.<sup>[35]</sup> The NBO calculations gave positive partial charges at Si between 0.20–0.33  $e$ . The Wiberg bond order for the Si–C bonds is in between 1.13 and 1.25, which indicates some double-bond character. The calculation of the electronic excitation of **2** using time-dependent DFT at the B3LYP/def2-TZVP level where the solvent influence was estimated with the polarized continuum model (PCM) produced a simulated UV/Vis spectrum (Figure S6 in the Supporting Information) which shows peaks at 406 and 497 nm. The signal at 497 nm comes from the  $\pi \rightarrow \pi^*$  (HOMO-1  $\rightarrow$  LUMO and HOMO  $\rightarrow$  LUMO + 1, Figure 2) excitation of the exocyclic Si–C orbitals. The signal at 406 nm is a mixture of excitations from the Si–Si bonding orbitals into vacant orbitals of the cAAC ligands (Table S4 and Figure S7 in the Supporting Information).

We also calculated the related carbene complex  $(\text{NHC}^{\text{Ph}})_3\text{Si}_3$  in which silicon and  $\text{NHC}^{\text{Ph}}$  should be more weakly bonded, because the cAAC is a stronger  $\sigma$  donor and a better  $\pi$  acceptor than  $\text{NHC}^{\text{Ph}}$ . The geometry of the latter is shown in Figure S5 in the Supporting information. The calculated Si–C bonds in  $(\text{NHC}^{\text{Ph}})_3\text{Si}_3$  are longer (1.947, 1.941, and 1.927 Å) than in **2** and the ligand-exchange reaction  $(\text{cAAC})_3\text{Si}_3 + 3\text{NHC}^{\text{Ph}} \rightarrow (\text{NHC}^{\text{Ph}})_3\text{Si}_3 + 3\text{cAAC}$  is endergonic by  $\Delta G = 20.9$  kcal mol $^{-1}$ . The bond dissociation energy (BDE) for loss of the cAAC ligands  $(\text{cAAC})_3\text{Si}_3 \rightarrow \text{Si}_3 + 3\text{cAAC}$  is 115.7 kcal mol $^{-1}$  at BP86/def2-SVP. A recalculation at M06-2X/def2-TZVPP//BP86/def2-SVP gives a value of 130.4 kcal mol $^{-1}$  which suggests an average BDE of  $D_e = 43.5$  kcal mol $^{-1}$  for each ligand.

In conclusion, more than six decades after spectroscopic detection of the  $\text{Si}_3$  cluster by Honig, the stable and isolable carbene-stabilized triatomic silicon(0) **2** has been synthesized in a simple synthetic procedure by controlling the reaction



**Figure 2.** Frontier molecular orbitals of **2** (B3LYP/def2-TZVP//BP86/def2-SVP). Hydrogen atoms are omitted for clarity.

conditions. The employment of cAAC carbene as a  $\pi$ -accepting ligand is crucial. Compound **2** is stable and isolable at room temperature under an inert atmosphere. It possesses a triangular  $\text{Si}_3$  unit with a lone pair of electrons on each silicon atom, and hence it can be also considered as a triangular trisilylene. The lone pair of electrons of each silicon atom is polarized toward carbene carbon atom because of the significant  $\pi$ -accepting properties of the cAAC ligand. This tris(cyclic alkyl(amino) carbene)trisilicon(0) might serve as a model for a better understanding of the formation of suspected silicon clusters in the interstellar medium. Additionally, the isolation of this molecule paves the way for the possible synthesis of other stable silicon(0) clusters which were previously thought to be unisolable under normal laboratory conditions and could be, until now, detected by mass spectrometry and characterized by correlating the spectroscopic data with theoretically calculated values.

### Experimental Section

**Synthesis of 2:** The adduct  $(\text{cAAC})\text{SiCl}_4$  (**1**) was placed in a flask and dissolved in THF at room temperature. THF was added to another flask containing four equivalents of potassium graphite ( $\text{KC}_8$ ). Both of these flasks were cooled to  $-107^\circ\text{C}$  by using THF/liquid nitrogen baths. The solution containing **1** was then added to a continuously stirred slurry of  $\text{KC}_8$  by cannula. The temperature of the mixture was slowly raised to  $-78^\circ\text{C}$  over 15 minutes and the resultant mixture was stirred at this temperature for another 30 minutes to obtain a dark-green solution. The temperature of this solution was slowly raised to  $-20^\circ\text{C}$  over two hours to produce a greenish-red solution which slowly changed to dark-red. Finally the solution was stirred for 9 hours at room temperature to obtain an air- and moisture-sensitive dark red-purple solution of **2**. The graphite was separated by filtration

and the product **2** was extracted with *n*-hexane which was stored at  $-32^{\circ}\text{C}$  in a freezer to form the dark rods of **2** in 25% yield. The dark red-purple crystals of **2** decompose above  $165^{\circ}\text{C}$  under an inert atmosphere. The UV/Vis spectrum of **2** (in *n*-hexane) shows absorption bands at 418 and 540 nm. Elemental analysis (%) found (calcd) for  $\text{C}_{60}\text{H}_{93}\text{N}_3\text{Si}_3$ : C, 76.72 (76.61); H, 9.79 (9.96); N, 4.52 (4.46).  $^1\text{H}$  NMR (500 MHz, 298 K,  $\text{C}_6\text{D}_6$ ):  $\delta = 7.13$  (m, 9H), 3.34–3.23 (m, 6H), 1.76 (s, 6H), 1.74 (d,  $J = 6.7$  Hz, 18H), 1.23 (d,  $J = 6.9$  Hz, 36H), 1.16 ppm (s, 18H).  $^{13}\text{C}$  NMR (126 MHz, 298 K,  $\text{C}_6\text{D}_6$ ):  $\delta = 207.08$ , 149.17, 137.98, 128.42, 128.29, 125.67, 69.57, 56.19, 50.81, 34.56, 31.92, 29.02, 28.47, 27.91, 25.38 ppm;  $^{29}\text{Si}$  NMR (99.395 MHz, 298 K,  $\text{C}_6\text{D}_6$ ):  $\delta = 7.20$  ppm;  $^{15}\text{N}$  NMR (50.709 MHz, 298 K,  $\text{C}_6\text{D}_6$ ):  $\delta = -233.0$  ppm. See reference [29] for the synchrotron radiation method, and the Supporting Information for theoretical calculations.

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